3.2x1.6mm INFRARED EMITTING DIODE

Part Number: KP-3216F3C

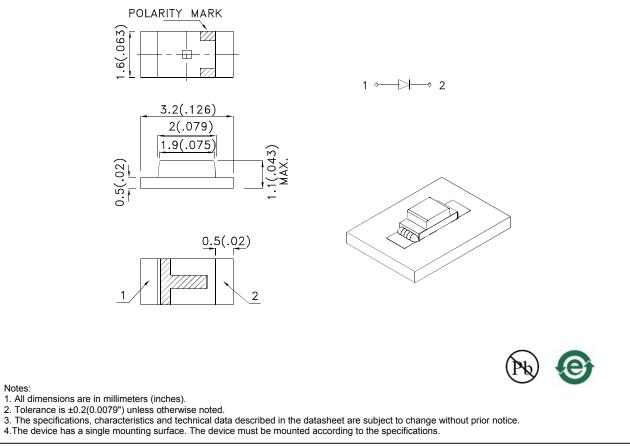
Features

- 3.2mmx1.6mm SMT LED,1.8mm thickness.
- Mechanically and spectrally matched to phototransistor.
- Wide viewing angle.
- Package: 2000pcs / reel.
- Moisture sensitivity level : level 3.
- RoHs compliant.

Description

F3 Made with Gallium Arsenide Infrared Emitting diodes.





SPEC NO: DSAA4438 APPROVED: WYNEC

Notes:

REV NO: V.13A CHECKED: Allen Liu DATE: JUL/03/2012 DRAWN: F.Cui

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Soloction Guido

Selection Guide					
Part No.	Dice	Lens Type	Po (mW/sr) [2] @ 20mA		Viewing Angle [1]
			Min.	Тур.	201/2
KP-3216F3C	F3 (GaAs)	Water Clear	1.2	3	120°
			*0.8	*2	

Notes:

01/2 is the angle from optical centerline where the luminous intensity is 1/2 of the optical peak value.
Radiant Intensity/ luminous flux: +/-15%.

*Radiant intensity value is traceable to the CIE127-2007 compliant national standards.

Electrical / Optical Characteristics at TA=25°C

Parameter	P/N	Symbol	Тур.	Max.	Units	Test Conditions
Forward Voltage [1]	F3	VF	1.2	1.6	V	I⊧=20mA
Reverse Current	F3	lr		10	uA	VR = 5V
Capacitance	F3	С	90		pF	VF=0V;f=1MHz
Peak Spectral Wavelength	F3	λP	940		nm	I⊧=20mA
Spectral Bandwidth	F3	Δλ1/2	50		nm	IF=20mA

Notes:

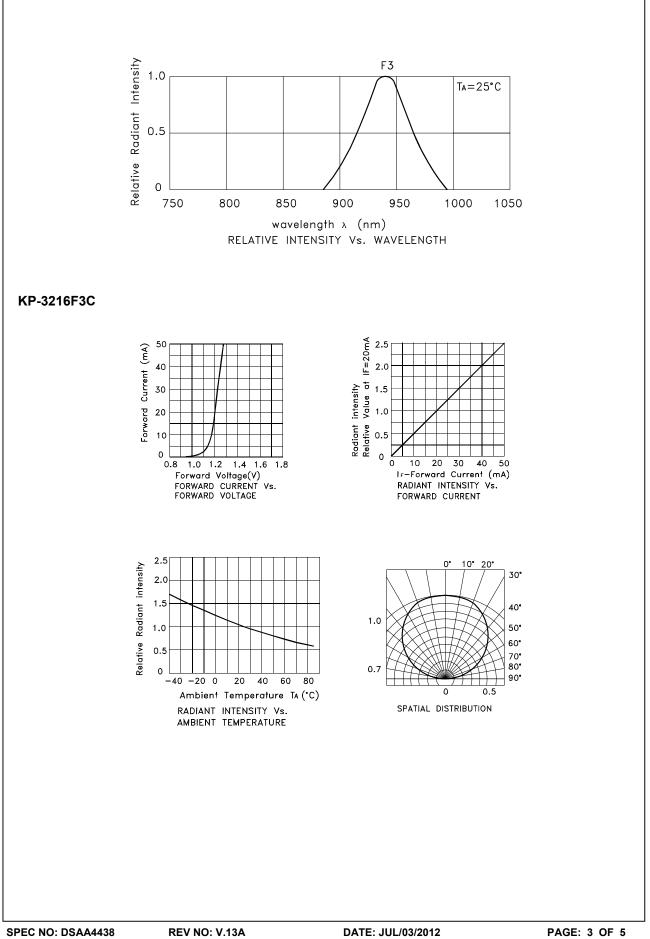
1. Forward Voltage: +/-0.1V.

2. Wavelength value is traceable to the CIE127-2007 compliant national standards.

Absolute Maximum Ratings at TA=25°C

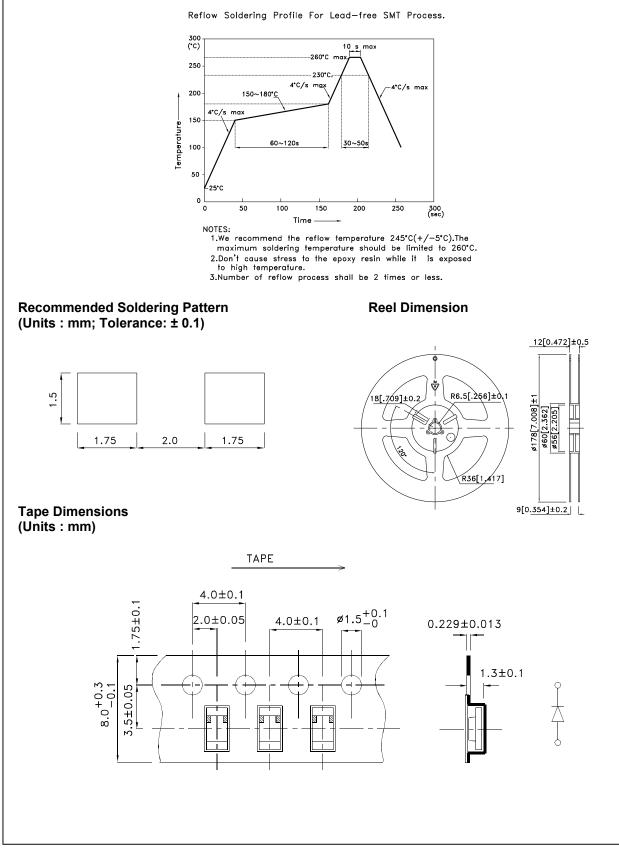
Parameter	Symbol	F3	Units
Power dissipation	PD	80	mW
DC Forward Current	lf	50	mA
Peak Forward Current [1]	ifs	1.2	A
Reverse Voltage	Vr	5	V
Operating Temperature	Та	-40 To +85	°C
Storage Temperature	Тятс	-40 To +85	°C

Note: 1. 1/100 Duty Cycle, 10µs Pulse Width.



KP-3216F3C

Reflow soldering is recommended and the soldering profile is shown below. Other soldering methods are not recommended as they might cause damage to the product.



DATE: JUL/03/2012 DRAWN: F.Cui

